

ABSTRACT

A polysilicon layer is formed on a dielectric layer positioned on a substrate. Then, the polysilicon layer is doped with first type dopants and second type dopants. Portions of the polysilicon layer and the dielectric layer are removed down to the surface of the substrate, so as to define at least a high resistance region and a low resistance region on the remainder of the polysilicon layer. Finally, a salicide layer is formed on the portions of the polysilicon layer within the low resistance region.